

DESCRIPTION:

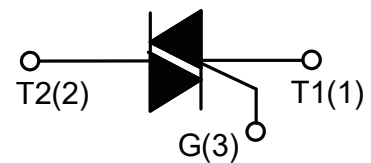
With high ability to withstand the shock loading of large current, T405-800B series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.



TO-252

MAIN FEATURES

Symbol	Value	Unit
V_{DRM}/V_{RRM}	600/800	V
$I_{T(RMS)}$	4	A


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40 - 150	°C
Operating junction temperature range	T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600/800	V
RMS on-state current TO-252 ($T_C=100^\circ\text{C}$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)	I_{TSM}	40	A
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	8	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	5	10	35	50	mA
V_{GT}		I - II -III	MAX	1.5				V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	10	20	50	70	mA
		II		15	35	60	80	
I_H	$I_T=100\text{mA}$		MAX	10	15	35	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	50	100	400	1000	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=5.5\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.75	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252	2.8	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient		70	

FIG.1: Maximum power dissipation versus RMS on-state current

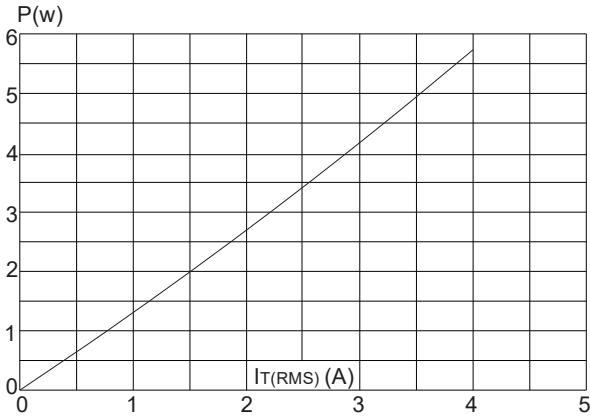


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35 μ m)(full cycle)

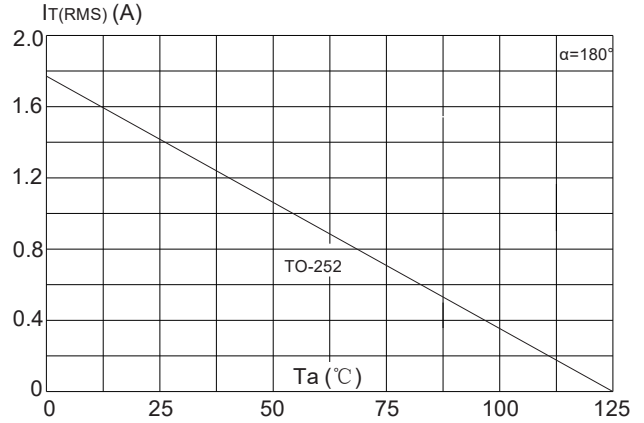


FIG.3: Surge peak on-state current versus number of cycles

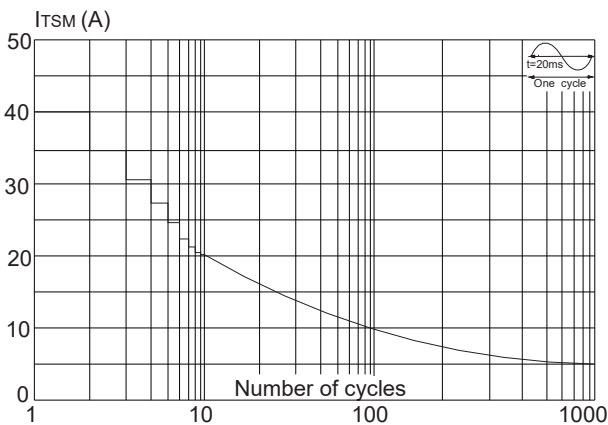


FIG.4: On-state characteristics (maximum values)

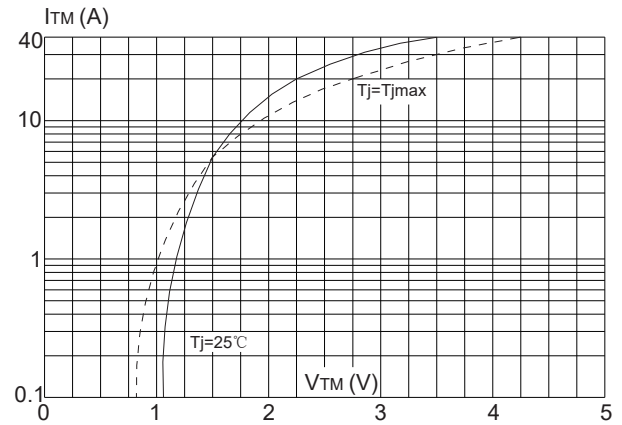
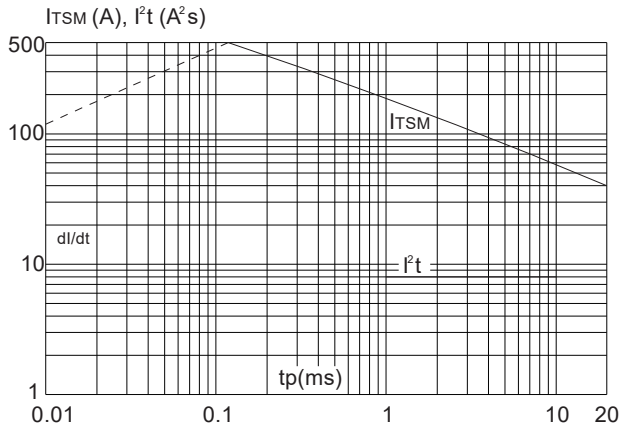
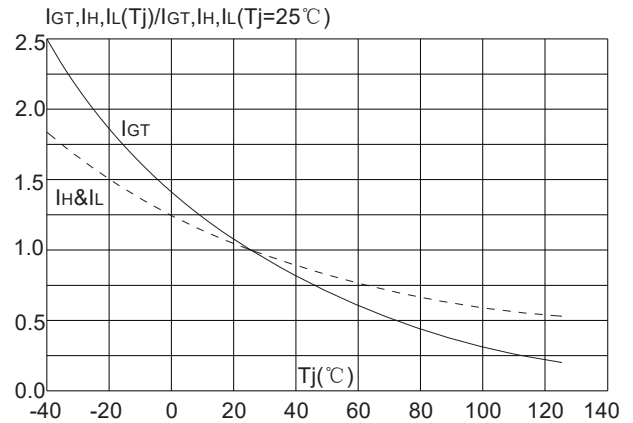


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(\text{min})}$)	+150°C
	-Temperature Max ($T_{s(\text{max})}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{s(\text{max})}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

